

## Product Overview

### FFPF08S60SN: 8A, 600V, STEALTH™ II Diode

For complete documentation, see the data sheet.

The FFPF08S60SN is a STEALTH™ II diode with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as freewheeling or boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

### Features

- Stealth recovery  $T_{rr} = 25\text{ns}$  (@ $I_F = 8\text{A}$ )
- Max Forward Voltage,  $V_F = 3.4\text{V}$  (@  $T_C = 25^\circ\text{C}$ )
- 600V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS compliant

### Applications

- AC-DC Merchant Power Supply - Desktop PC
- LCD TV

Part Electrical Specifications											
Product	Pricing (\$/Unit)	Compliance	Status	Type	$I_{O(\text{rec})}$ Max (A)	$t_{rr}$ Max (ns)	$V_{RRM}$ Max (V)	$V_{FM}$ Max (V)	$I_{FSM}$ Max (A)	$I_R$ Max (mA)	Package Type
FFPF08S60SNTU	0.3333	Pb-free Halide free	Active	Single	8	25	600	3.4	60	0.1	TO-220 FP / TO-220F-2FS

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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